	Type	Hits	Search Text	DBs
1	BRS	81357	complementary adj (metal adj oxide adj semiconducor adj (fet or field)) or cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	110	brewster-william-m.xa.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	3287	thicken$4 near8 (oxide or gate near2 (insulat$4 or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	243	(complementary adj (metal adj oxide adj semiconducor adj (fet or field)) or cmos) and (thicken$4 near8 (oxide or gate near2 (insulat$4 or dielectric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	46824	second! near4 (mask$4 or resist or pr or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	116891	implant or inplant or inplanting or implanting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	81357	complementary adj (metal adj oxide adj semiconducor adj (fet or field)) or cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	78784	(thick$4 or grow$4) near4 (oxide or gate near2 (insulat$4 or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
9 BRS	1930	(second! near4 (mask$4 or resist or pr or photoresist)) and (inplant or implant or inplanting or implanting) and (complementary adj (metal adj oxide adj semiconducor adj (fet or field)) or cmos) and ((thick$4 or grow$4) near4 (oxide or gate near2 (insulat$4 or dielectric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10 BRS	3069	(second! near4 (mask$4 or resist or pr or photoresist)) same (inplant or implant or inplanting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11 BRS	366	((second! near4 (mask$4 or resist or pr or photoresist)) same (inplant or implant or inplanting)) same ((thick$4 or grow$4) near4 (oxide or gate near2 (insulat$4 or dielectric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12 BRS	136	(((second! near4 (mask$4 or resist or pr or photoresist)) same (inplant or implant or inplanting)) same ((thick$4 or grow$4) near4 (oxide or gate near2 (insulat$4 or dielectric)))) and (complementary adj (metal adj oxide adj semiconducor adj (fet or field)) or cmos)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13 BRS	243	(complementary adj (metal adj oxide adj semiconducor adj (fet or field)) or cmos) and (thicken$4 near8 (oxide or gate near2 (insulat$4 or dielectric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
14 BRS	133	(((((second! near4 (mask$4 or resist or pr or photoresist)) same (inplant or implant or inplanting or implanting)) same ((thick$4 or grow$4) near4 (oxide or gate near2 (insulat$4 or dielectric)))) and (complementary adj (metal adj oxide adj semiconductor adj (fet or field)) or cmos) and ((complementary adj (metal adj oxide adj semiconducor adj (fet or field)) or cmos) and (thicken$4 near8 (oxide or gate near2 (insulat$4 or dielectric)))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15 BRS	114	(((((second! near4 (mask$4 or resist or pr or photoresist)) same (inplant or implant or inplanting or implanting)) same ((thick$4 or grow$4) near4 (oxide or gate near2 (insulat$4 or dielectric)))) and (complementary adj (metal adj oxide adj semiconductor adj (fet or field)) or cmos) not ((complementary adj (metal adj oxide adj semiconducor adj (fet or field)) or cmos) and (thicken$4 near8 (oxide or gate near2 (insulat$4 or dielectric)))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16 IS&R	438	(438/981).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17 BRS	252	((438/981).CCLS.) and (@ay < "2000")	USPAT
18 BRS	469291	polysilicon or poly or polysi or polisilicon or poli	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19 BRS	3938	(second! near4 (mask$4 or resist or pr or photoresist)) same (polysilicon or poly or polysi or polisilicon or poli)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
20	BRS	2128	(second! near4 (mask$4 or resist or pr or photoresist)) near8 (polysilicon or poly or polysi or polisilicon or poli)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	31008	second! near2 (mask$4 or resist or pr or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	1330	(second! near2 (mask$4 or resist or pr or photoresist)) near8 (polysilicon or poly or polysi or polisilicon or poli)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	227	((second! near2 (mask$4 or resist or pr or photoresist)) near8 (polysilicon or poly or polysi or polisilicon or poli)) same (inplant or implant or inplanting or implanting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	77	(((second! near2 (mask$4 or resist or pr or photoresist)) near8 (polysilicon or poly or polysi or polisilicon or poli)) same (inplant or implant or inplanting or implanting)) and (complementary adj (metal adj oxide adj semiconducor adj (fet or field)) or cmos) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	44236	eeprom or eporm or electric$4 adj program$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
26	BRS	37	(((second! near2 (mask$4 or resist or pr or photoresist)) near8 (polysilicon or poly or polysi or polisilicon or poli)) same (inplant or implant or inplanting or implanting)) and (eeprom or eporm or electric$4 adj program$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
27 BRS	27	(((((second! near2 (mask$4 or resist or pr or photoresist)) near8 (polysilicon or poly or polysi or polisilicon or poli)) same (inplant or implant or inplanting or implanting)) and (eeprom or eporm or electric$4 adj program$4)) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
28 BRS	1200679	sio? or "sio.sub.2" or oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
29 BRS	1145158	oxidizing or oxidation or grow$4 or thicken$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
30 BRS	6349	plasma near12 bias$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
31 BRS	607085	nitrogen or "n.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
32 BRS	121646	(nitrog$4 near2 (oxygen or oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
33 BRS	152617	(nitrog$4 near2 (oxygen or oxide)) or (no near2 gas$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
34 BRS	162096	(degree or deg?) near2 ("100" or "150" or "200" or "250")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
35 BRS	0	(plasma near12 bias$4) same (oxidizing or oxidation or grow$4 or thicken$4) same ((nitrog$4 near2 (oxygen or oxide)) or (no near2 gas$4)) same ((degree or deg?) near2 ("100" or "150" or "200" or "250"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
36 BRS	310108	plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
37 BRS	10	plasma same (oxidizing or oxidation or grow$4 or thicken$4) same ((nitrog$4 near2 (oxygen or oxide)) or (no near2 gas$4)) same ((degree or deg?) near2 ("100" or "150" or "200" or "250"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
38 BRS	311126	plasma or pecvd or pcvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
39 BRS	30	(plasma or pecvd or pcvd) same ((nitrog$4 near2 (oxygen or oxide)) or (no near2 gas$4)) same ((degree or deg?) near2 ("100" or "150" or "200" or "250"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
40 BRS	20	(plasma or pecvd or pcvd) same (oxidizing or oxidation or grow$4 or thicken$4) same ((nitrog$4 near2 (oxygen or oxide)) or (no near2 gas$4)) not (plasma same (oxidizing or oxidation or grow$4 or thicken$4) same ((nitrog$4 near2 (oxygen or oxide)) or (no near2 gas$4)) same ((degree or deg?) near2 ("100" or "150" or "200" or "250")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
41 BRS	18	(((plasma or pecvd or pcvd) same ((nitrog$4 near2 (oxygen or oxide)) or (no near2 gas$4)) same ((degree or deg?) near2 ("100" or "150" or "200" or "250"))) not (plasma same (oxidizing or oxidation or grow$4 or thicken$4) same ((nitrog$4 near2 (oxygen or oxide)) or (no near2 gas$4)) same ((degree or deg?) near2 ("100" or "150" or "200" or "250")))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
42 BRS	252	(complementary adj (metal adj (insulator or oxide) adj semiconducor adj (fet or field)) or cmos or cmis) and (thicken$4 near8 (oxide or gate near2 (insulat$4 or dielectric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
43 BRS	11111	(inplant or implant or inplanting or implanting) same (resist or photoresist or pr)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
44 BRS	4799	(plasma or pecvd or pcvd) same gate near3 (insulator or (sio? or "sio.sub.2" or oxide) or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
45 BRS	86095	(complementary adj (metal adj (insulator or oxide) adj semiconducor adj (fet or field)) or cmos or cmis)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
46 BRS	8	((complementary adj (metal adj (insulator or oxide) adj semiconducor adj (fet or field)) or cmos or cmis)) same ((plasma or pecvd or pcvd) same gate near3 (insulator or (sio? or "sio.sub.2" or oxide) or dielectric)) same ((inplant or implant or inplanting or implanting) same (resist or photoresist or pr))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type		Hits	Search Text	DBs
47	BRS	421	((complementary adj (metal adj (insulator or oxide) adj semiconducor adj (fet or field)) or cmos or cmis)) and ((plasma or pecvd or pcvd) same gate near3 dielectric)) and ((inplant or implant or inplanting or implanting) same (resist or photoresist or pr))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
48	BRS	336	(((complementary adj (metal adj (insulator or oxide) adj semiconducor adj (fet or field)) or cmos or cmis)) and ((plasma or pecvd or pcvd) same gate near3 dielectric)) and ((insulator or (sio? or "sio.sub.2" or oxide) or dielectric)) and ((inplant or implant or inplanting or implanting) same (resist or photoresist or pr))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
49	BRS	982	(plasma or pecvd or pcvd) near6 gate near3 (insulator or (sio? or "sio.sub.2" or oxide) or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
50	BRS	62	(((complementary adj (metal adj (insulator or oxide) adj semiconducor adj (fet or field)) or cmos or cmis)) and ((plasma or pecvd or pcvd) near6 gate near3 (insulator or (sio? or "sio.sub.2" or oxide) or dielectric)) and ((inplant or implant or inplanting or implanting) same (resist or photoresist or pr))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
51	BRS	49	(((complementary adj (metal adj (insulator or oxide) adj semiconducor adj (fet or field)) or cmos or cmis)) and ((plasma or pecvd or pcvd) near6 gate near3 (insulator or (sio? or "sio.sub.2" or oxide) or dielectric)) and ((inplant or implant or inplanting or implanting) same (resist or photoresist or pr))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
52	BRS	15577	plasma adj enhanc$4 or pecvd or pcvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
53	BRS	138	(plasma adj enhanc$4 or pecvd or pcvd) near3 gate near3 (insulator or (sio? or "sio.sub.2" or oxide) or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
54	BRS	4	((complementary adj (metal adj (insulator or oxide) adj semiconducor adj (fet or field)) or cmos or cmis) and ((plasma adj enhanc$4 or pecvd or pcvd) near6 gate near3 (insulator or (sio? or "sio.sub.2" or oxide) or dielectric)) and ((inplant or implant or inplanting or implanting) same (resist or photoresist or pr))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
55	IS&R	834	((438/154) or (438/788) or (438/791)).CCLS.	USPAT; US-PGPUB
56	IS&R	0	("9662004.ap.").PN.	USPAT
57	IS&R	0	("9662004.ap.").PN.	USPAT; US-PGPUB
58	BRS	0	09662004.ap.	USPAT
59	BRS	0	09662004.ap.	USPAT; US-PGPUB
60	BRS	0	9662004.ap.	USPAT; US-PGPUB
61	BRS	4023	plasma near2 (bias$4 or DC)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
62	BRS	113537	gate near2 (insulat$4 or dielectric or oxide or "sio.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
63	BRS	7	(plasma near2 (bias$4 or DC)) near8 (gate near2 (insulat$4 or dielectric or oxide or "sio.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
64	BRS	0	(plasma near2 (bias$4 or DC)) near8 oxidiz$4 near4 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
65	BRS	0	(plasma near2 (bias$4 or DC)) same oxidiz$4 near4 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
66	BRS	1	plasma near8 (bias$4 or DC) same oxidiz$4 near4 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
67	BRS	174	plasma near8 (bias$4 or DC) same oxidiz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
68	BRS	1262893	sio? or "sio.sub.2" or oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
69	BRS	1	plasma near8 (bias$4 or DC) near8 oxidiz$4 near8 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
70	BRS	44	plasma near8 (bias$4 or DC) near8 oxidiz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
71	BRS	25	(plasma near8 (bias$4 or DC) near8 oxidiz$4) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
72	BRS	2	plasma near8 anodic$4 near8 oxidiz$4 near8 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
73	BRS	5	plasma near8 anod$6 near8 oxidiz$4 near8 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
74	BRS	134	plasma near8 (bias$4 or DC or anod$6) near8 oxidiz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
75	BRS	77	plasma near4 (bias$4 or DC or anod$6) near4 oxidiz$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
76	BRS	64	(plasma near4 (bias$4 or DC or anod$6) near4 oxidiz$4) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
77	BRS	165037	mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
78	BRS	7	((plasma near4 (bias$4 or DC or anod$6) near4 oxidiz$4) and (@ay < "2000")) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
79	BRS	9	(plasma near8 (bias$4 or DC or anod$6) near8 oxidiz$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
80	BRS	2	((plasma near8 (bias$4 or DC or anod$6) near8 oxidiz$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) not (((plasma near4 (bias$4 or DC or anod$6) near4 oxidiz$4) and (@ay < "2000")) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
81	BRS	0	(pecvd near4 (bias$4 or DC or anod$6) near4 oxidiz$4) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
82	BRS	0	(pecvd near8 (bias$4 or DC or anod$6) near8 oxidiz$4) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
83	BRS	10	(pecvd same (bias$4 or DC or anod$6) same oxidiz$4) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
84	BRS	8	((hdpcvd or hdp) same (bias$4 or DC or anod$6) same oxidiz$4) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
85	BRS	4	(((hdpcvd or hdp) same (bias$4 or DC or anod$6) same oxidiz$4) and (@ay < "2000")) not ((pecvd same (bias$4 or DC or anod$6) same oxidiz$4) and (@ay < "2000"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
86	BRS	59	((plasma same (bias$4 or DC or anod$6) same oxidiz$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ay < "2000"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
87	BRS	24	((plasma same (bias$4 or DC or anod$6) same oxidiz$4 same gate) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ay < "2000"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
88	BRS	1650037	(mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
89	BRS	106	(plasma same (bias$4 or DC or anod$6) same oxidiz$4 same gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type		Hits	Search Text	DBs
90	BRS	82	(plasma same (bias$4 or DC or anod$6) same oxidiz$4 same gate) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
91	IS&R	1009	((438/154) or (438/788) or (438/791) or (438/771)).CCLS.	USPAT; US-PGPUB